SIEMENS

Silicon N Channel MOSFET Tetrode — BF 998

Features

- Short-channel transistor with high S/C quality factor
- For low-noise, gain-controlled input stages up to 1 GHz

5:1

Type	Marking	Ordering Code (tape and reel)	Pin Configuration 1	2	3	4	Package[1]
BF 998	MO	Q62702-F1129	S	D	G_2	G_1	SOT-143

Maximum Ratings

Parameter	Symbol	Values	Unit
Drain-source voltage	V_{DS}	12	V
Drain current	I_D	30	mA
Gate 1/gate 2 peak source current	$\pm I_{G1/2SM}$	10	
Total power dissipation, $T_S < 76$ °C	P_{tot}	200	mW
Storage temperature range	T_{stg}	– 55 ... + 150	°C
Channel temperature	T_{ch}	150	

Thermal Resistance

Junction - soldering point	$R_{th\,JS}$	< 370	K/W

[1] For detailed information see chapter Package Outlines.

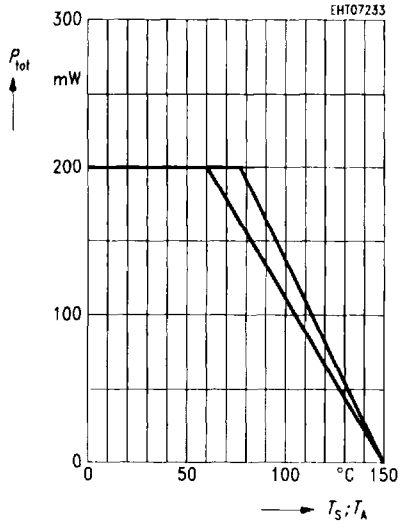
Electrical Characteristics
at T_A = 25 °C, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Drain-source breakdown voltage I_D = 10 µA, V_{G1S} = − V_{G2S} = 4 V	$V_{(BR)DS}$	12	–	–	V
Gate 1-source breakdown voltage ± I_{G1S} = 10 mA, V_{G2S} = V_{DS} = 0	± $V_{(BR)G1SS}$	8	–	12	
Gate 2-source breakdown voltage ± I_{G2S} = 10 mA, V_{G1S} = V_{DS} = 0	± $V_{(BR)G2SS}$	8	–	12	
Gate 1-source leakage current ± V_{G1S} = 5 V, V_{G2S} = V_{DS} = 0	± I_{G1SS}	–	–	50	nA
Gate 2-source leakage current ± V_{G2S} = 5 V, V_{G1S} = V_{DS} = 0	± I_{G2SS}	–	–	50	
Drain current V_{DS} = 8 V, V_{G1S} = 0, V_{G2S} = 4 V	I_{DSS}	2	–	18	mA
Gate 1-source pinch-off voltage V_{DS} = 8 V, V_{G2S} = 4 V, I_D = 20 µA	$V_{G1S(p)}$	–	–	2.5	V
Gate 2-source pinch-off voltage V_{DS} = 8 V, V_{G1S} = 0, I_D = 20 µA	$V_{G2S(p)}$	–	–	2	

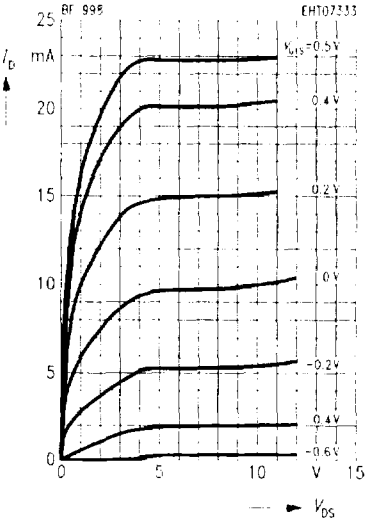
Electrical Characteristics
at T_A = 25 °C, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Forward transconductance V_{DS} = 8 V, I_D = 10 mA, V_{G2S} = 4 V f = 1 kHz	g_{fs}	–	24	–	mS
Gate 1 input capacitance V_{DS} = 8 V, I_D = 10 mA, V_{G2S} = 4 V f = 1 MHz	C_{g1ss}	–	2.1	2.5	pF
Gate 2 input capacitance V_{DS} = 8 V, I_D = 10 mA, V_{G2S} = 4 V f = 1 MHz	C_{g2ss}	–	1.2	–	
Reverse transfer capacitance V_{DS} = 8 V, I_D = 10 mA, V_{G2S} = 4 V f = 1 MHz	C_{dg1}	–	25	–	fF
Output capacitance V_{DS} = 8 V, I_D = 10 mA, V_{G2S} = 4 V f = 1 MHz	C_{dss}	–	1.05	–	pF
Power gain (test circuit 1) V_{DS} = 8 V, I_D = 10 mA, f = 200 MHz, G_G = 2 mS, G_L = 0.5 mS, V_{G2S} = 4 V	G_{ps}	–	28	–	dB
Power gain (test circuit 2) V_{DS} = 8 V, I_D = 10 mA, f = 800 MHz, G_G = 3.3 mS, G_L = 1 mS, V_{G2S} = 4 V	G_{ps}	–	20	–	
Noise figure (test circuit 1) V_{DS} = 8 V, I_D = 10 mA, f = 200 MHz, G_G = 2 mS, G_L = 0.5 mS, V_{G2S} = 4 V	F	–	0.6	–	dB
Noise figure (test circuit 2) V_{DS} = 8 V, I_D = 10 mA, f = 800 MHz, G_G = 3.3 mS, G_L = 1 mS, V_{G2S} = 4 V	F	–	1	–	
Control range (test circuit 2) V_{DS} = 8 V, V_{G2S} = 4 ... – 2 V f = 800 MHz	ΔG_{ps}	40	–	–	

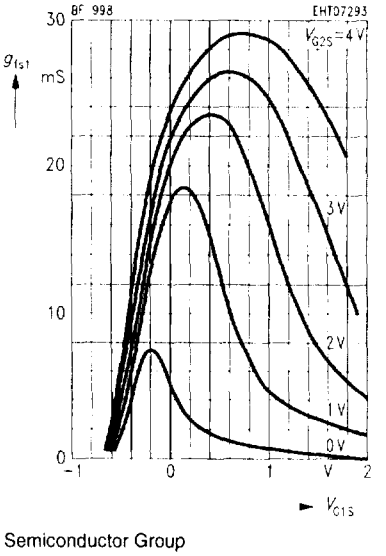
Total power dissipation $P_{tot} = f(T_A)$



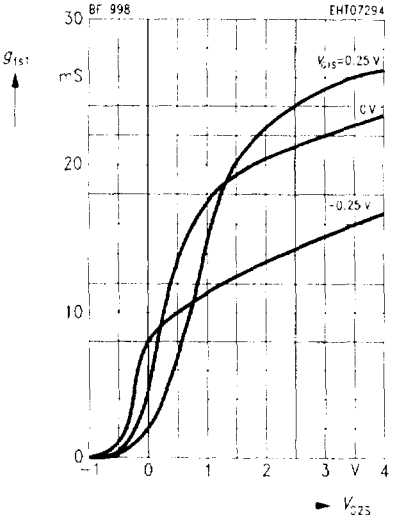
Output characteristics $I_D = f(V_{DS})$
V_{G2S} = 4 V



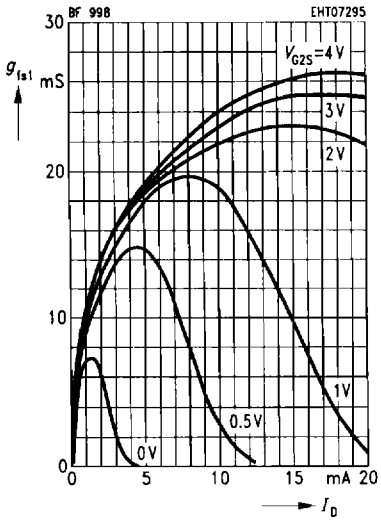
Gate 1 forward transconductance
$g_{fs1} = f(V_{G1S})$
V_{DS} = 8 V, I_{DSS} = 10 mA, f = 1 kHz



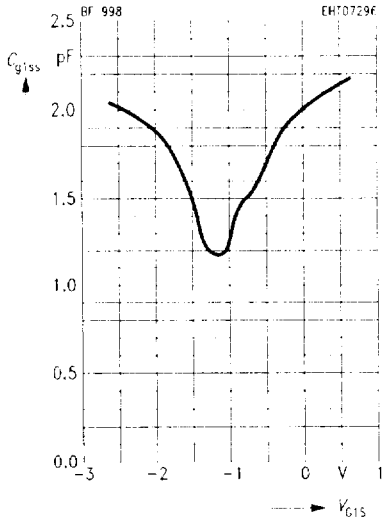
Gate 1 forward transconductance
$g_{fs1} = f(V_{G2S})$
V_{DS} = 8 V, I_{DSS} = 10 mA, f = 1 kHz



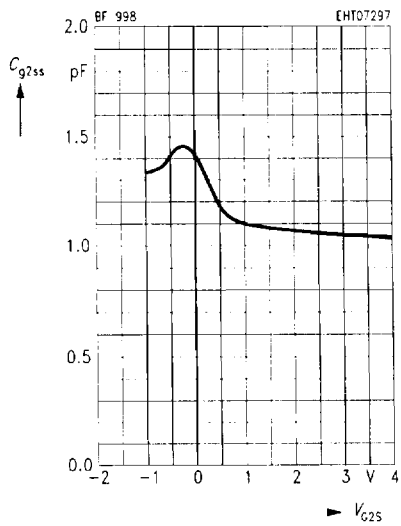
Gate 1 forward transconductance
$g_{fs1} = f(I_D)$
V_{DS} = 8 V, I_{DSS} = 10 mA, f = 1 kHz



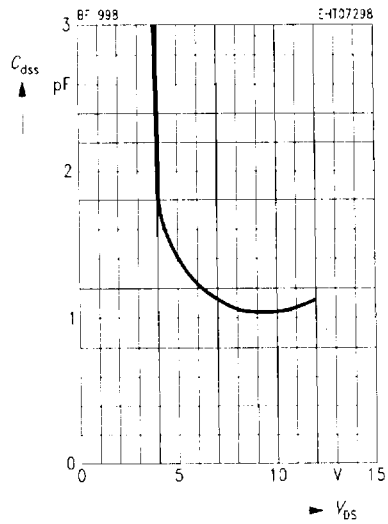
Gate 1 input capacitance $C_{g1ss} = f(V_{G1S})$
V_{G2S} = 4 V, V_{DS} = 8 V, I_{DSS} = 10 mA,
f = 1 MHz



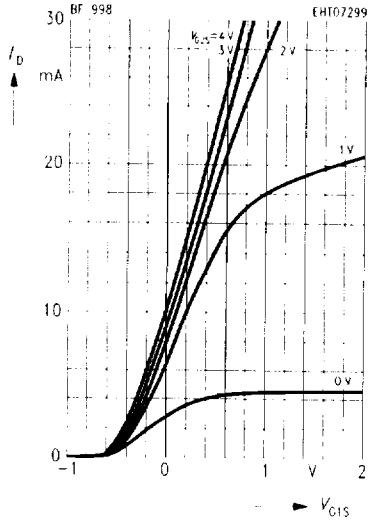
Gate 2 input capacitance $C_{g2ss} = f(V_{G2S})$
V_{G1S} = 0 V, V_{DS} = 8 V
I_{DSS} = 10 mA, f = 1 MHz



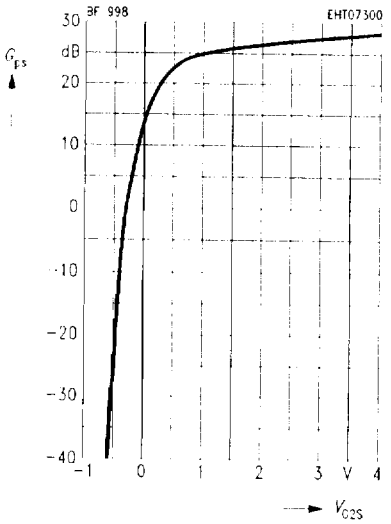
Output capacitance $C_{dss} = f(V_{DS})$
V_{G1S} = 0 V, V_{G2S} = 4 V
I_{DSS} = 10 mA, f = 1 MHz



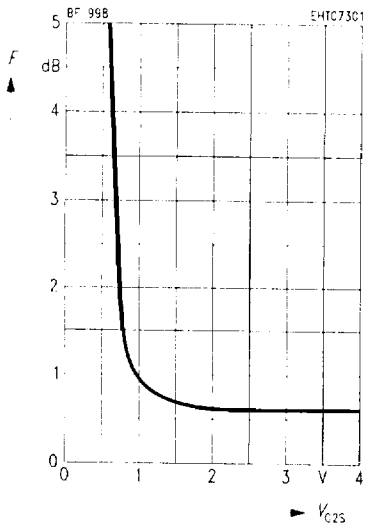
Drain current $I_D = f(V_{G1S})$
V_{DS} = 8 V



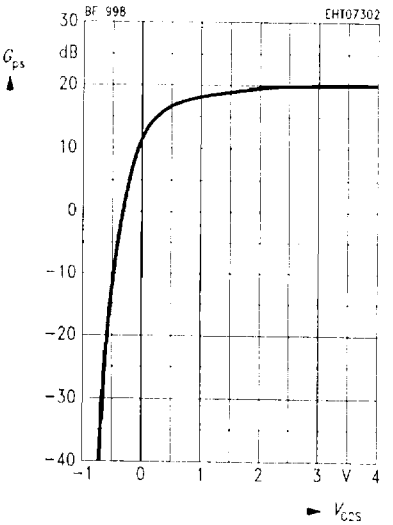
Power gain $G_{ps} = f(V_{G2S})$
V_{DS} = 8 V, V_{G1S} = 0, I_{DSS} = 10 mA,
f = 200 MHz (see test circuit 1)



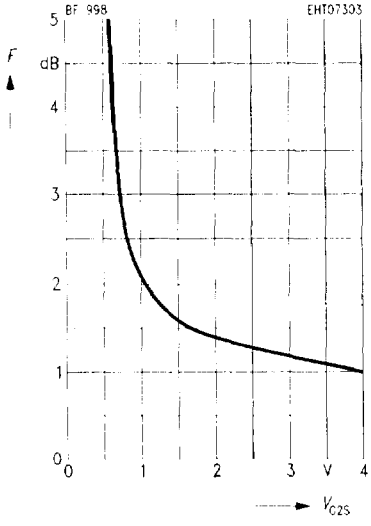
Noise figure $F = f(V_{G2S})$
V_{DS} = 8 V, V_{G1S} = 0, I_{DSS} = 10 mA,
f = 200 MHz (see test circuit 1)



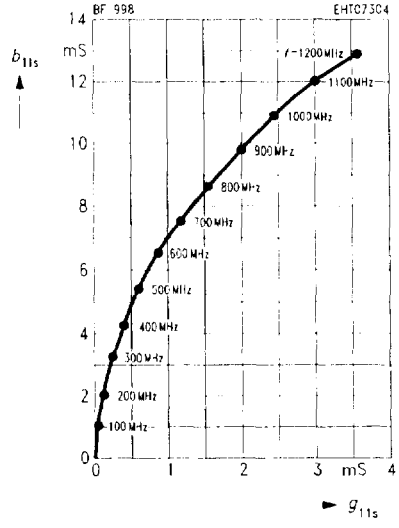
Power gain $G_{ps} = f(V_{G2S})$
V_{DS} = 8 V, V_{G1S} = 0, I_{DSS} = 10 mA,
f = 800 MHz (see test circuit 2)



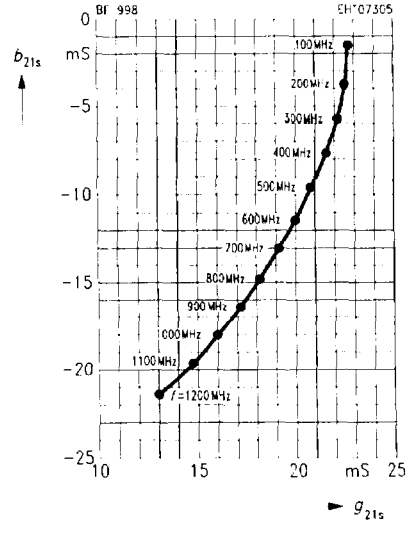
Noise figure $F = f(V_{G2S})$
V_{DS} = 8 V, V_{G1S} = 0, I_{DSS} = 10 mA,
f = 800 MHz (see test circuit 2)



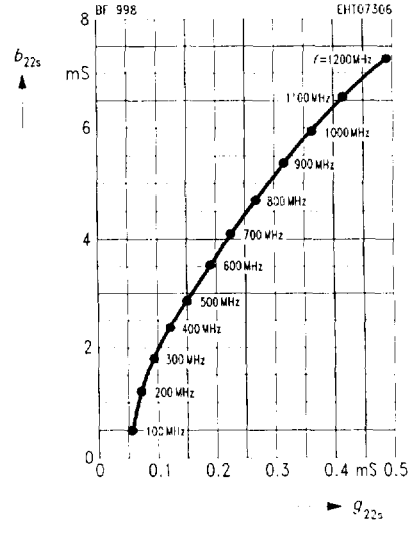
Gate 1 input admittance y_{11s}
V_{DS} = 8 V, V_{G2S} = 4 V, V_{G1S} = 0,
I_{DSS} = 10 mA (common-source)



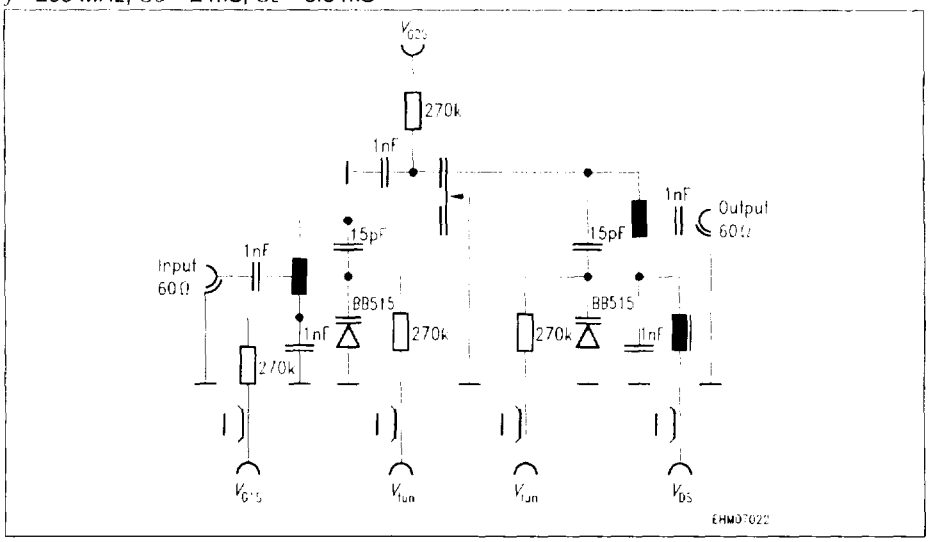
Gate 1 forward transfer admittance y_{21s}
V_{DS} = 8 V, V_{G2S} = 4 V, V_{G1S} = 0
I_{DSS} = 10 mA (common-source)



Output admittance y_{22s}
V_{DS} = 8 V, V_{G2S} = 4 V, V_{G1S} = 0
I_{DSS} = 10 mA (common-source)



Test circuit 1 for power gain and noise figure
f = 200 MHz, G_G = 2 mS, G_L = 0.5 mS



Test circuit 2 for power gain and noise figure
f = 800 MHz, G_G = 3.3 mS, G_L = 1 mS